

Docket No.: GR 95 P 1411

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : GUNTER PLASA
Filed : Concurrently herewith
Title : METHOD FOR PRODUCING A MEMORY CELL

#4
6-15-98
T. T.

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent No. 5,109,258 (Redwine), dated April 28, 1992;

U.S. Patent No. 4,400,867 (Fraser), dated August 30, 1983;

German Published, Non-Prosecuted Application No. 27 39 662 (Murrmann), dated March 8, 1979, pertains to a method for producing MOS transistors;

German Published, Non-Prosecuted Application No. 25 20 047 (Antipov), dated December 4, 1975, pertains to a method for producing silicon gate field effect transistors;

Published European Patent Application No. 0 294 699 A2 (Mazzali), dated December 14, 1988;

Published Japanese Patent Application No. 57-42169, dated March 9, 1982, as mentioned on page 3 of the specification;

Japanese Patent Abstract No. 61-248532 (Mitsui), dated November 5, 1986;

IEEE Transactions on Electron Devices, October 1984, Volume ED-31, Number 10;

IEEE Transactions on Electron Devices, January 1981, Volume ED-28, Number 1;
and

"Formation of High Quality Storage Capacitor Dielectrics by in-situ Rapid Thermal Reoxidation of Si_3N_4 Films in N_2O Ambient", IEEE Electron Device Letters, Vol. 15, No. 8, August 1994, pp. 266-268.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



For Applicant

LAURENCE A. GREENBERG
REG. NO. 29,308

Date: February 9, 1998

Lerner and Greenberg, P.A.
Post Office Box 2480
Hollywood, FL 33022-2480
Tel: (954) 925-1100
Fax: (954) 925-1101

/tg